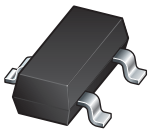


PMV30XN

20 V, 3.2 A N-channel Trench MOSFET

Rev. 1 — 22 June 2011 Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

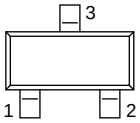
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	T_j = 25 °C		-	-	20	V
V_{GS}	gate-source voltage			-12	-	12	V
I_D	drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C	[1]	-	-	3.2	A
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 3.2 A; T_j = 25 °C		-	28	35	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm^2.

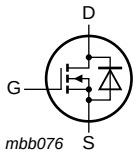
2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	S	source		
3	D	drain		



SOT23 (TO-236AB)



3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMV30XN	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking codes

Type number	Marking code[1]
PMV30XN	NZ%

[1] % = placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T_j = 25 °C		-	20	V
V_{GS}	gate-source voltage			-12	12	V
I_D	drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C	[1]	-	3.2	A
		V_{GS} = 4.5 V; T_{amb} = 100 °C	[1]	-	2.1	A
I_{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \leq 10$ µs		-	12.8	A
P_{tot}	total power dissipation	T_{amb} = 25 °C	[2]	-	380	mW
			[1]	-	520	mW
		T_{sp} = 25 °C		-	1800	mW
T_j	junction temperature			-55	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C
Source-drain diode						
I_S	source current	T_{amb} = 25 °C	[1]	-	0.6	A

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm^2.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	20	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = 250 µA; V_{DS} = V_{GS}; T_j = 25 °C	0.5	1	1.5	V
I_{DSS}	drain leakage current	V_{DS} = 20 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	µA
		V_{DS} = 20 V; V_{GS} = 0 V; T_j = 150 °C	-	-	10	µA
I_{GSS}	gate leakage current	V_{GS} = 12 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -12 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 3.2 A; T_j = 25 °C	-	28	35	mΩ
		V_{GS} = 4.5 V; I_D = 3.2 A; T_j = 150 °C	-	44	51	mΩ
		V_{GS} = 2.5 V; I_D = 2.6 A; T_j = 25 °C	-	39	60	mΩ
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 3 A; T_j = 25 °C	-	15	-	S
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	V_{DS} = 15 V; I_D = 3 A; V_{GS} = 4.5 V; T_j = 25 °C	-	4.9	7.4	nC
Q_{GS}	gate-source charge		-	1.5	-	nC
Q_{GD}	gate-drain charge		-	2.9	-	nC
C_{iss}	input capacitance	V_{DS} = 15 V; f = 1 MHz; V_{GS} = 0 V; T_j = 25 °C	-	420	-	pF
C_{oss}	output capacitance		-	125	-	pF
C_{rss}	reverse transfer capacitance		-	73	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 15 V; V_{GS} = 4.5 V; $R_{G(ext)}$ = 6 Ω; T_j = 25 °C; I_D = 3 A	-	11	-	ns
t_r	rise time		-	28	-	ns
$t_{d(off)}$	turn-off delay time		-	93	-	ns
t_f	fall time		-	51	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	I_S = 0.6 A; V_{GS} = 0 V; T_j = 25 °C	-	0.67	1.2	V